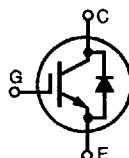


Low $V_{CE(sat)}$ IGBT with Diode
High speed IGBT with Diode

IXGH 30N60U1
IXGH 30N60AU1

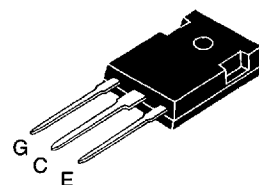
V_{CES}	I_{C25}	$V_{CE(sat)}$
600 V	50 A	2.5 V
600 V	50 A	3.0 V

Combi Packs



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	50	A
I_{C90}	$T_C = 90^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	100	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 33\ \Omega$ Clamped inductive load, $L = 100\ \mu\text{H}$	$I_{CM} = 60$ @ $0.8\ V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	200	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight		6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-247 AD
- IGBT and anti-parallel FRED in one package
- 2nd generation HDMOST™ process
- Low $V_{CE(sat)}$
 - for low on-state conduction losses
- MOS Gate turn-on
 - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
 - soft recovery with low I_{RM}

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

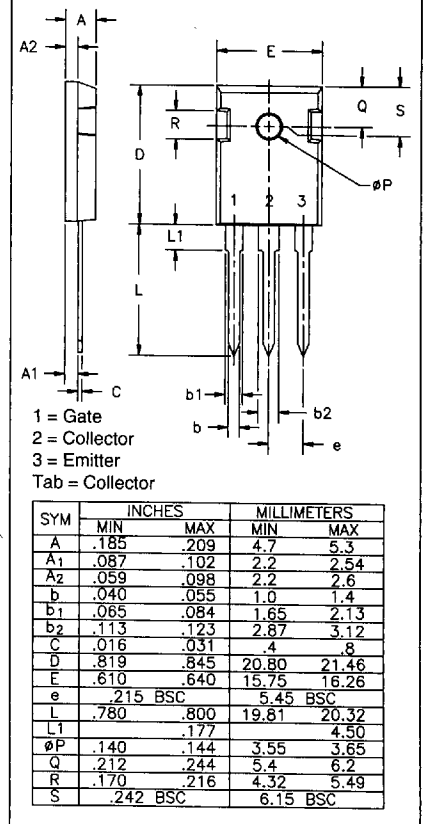
Advantages

- Space savings (two devices in one package)
- Easy to mount with 1 screw (isolated mounting screw hole)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 750\ \mu\text{A}$, $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$			500 μA 8 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$			2.5 V 3.0 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	8	16	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		2800	pF
C_{oes}			290	pF
C_{res}			70	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		150	nC
Q_{ge}			35	nC
Q_{gc}			60	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 300\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 33\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		100	ns
t_{ri}			200	ns
$t_{d(off)}$			500	ns
t_{fi}		30N60AU1	200	ns
E_{off}		30N60AU1	2	mJ
$t_{d(on)}$			100	ns
t_{ri}	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 300\text{ }\mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 33\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		200	ns
E_{on}			3	mJ
$t_{d(off)}$			600	ns
t_{fi}		30N60U1	500	ns
		30N60AU1	250	ns
E_{off}		30N60U1	5.5	mJ
		30N60AU1	4.0	mJ
R_{thJC}				0.62 K/W
R_{thCK}			0.25	K/W

TO-247 AD Outline



Reverse Diode (FRED)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = I_{C90}$, $V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			1.6 V
I_{RM}	$I_F = I_{C90}$, $V_{GE} = 0\text{ V}$, $-di_F/dt = 240\text{ A}/\mu\text{s}$ $V_R = 360\text{ V}$, $T_J = 125^\circ\text{C}$ $I_F = 1\text{ A}$; $-di_F/dt = 100\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$, $T_J = 25^\circ\text{C}$		10	15 A
t_{rr}			150	ns
			35	ns
R_{thJC}				1 K/W

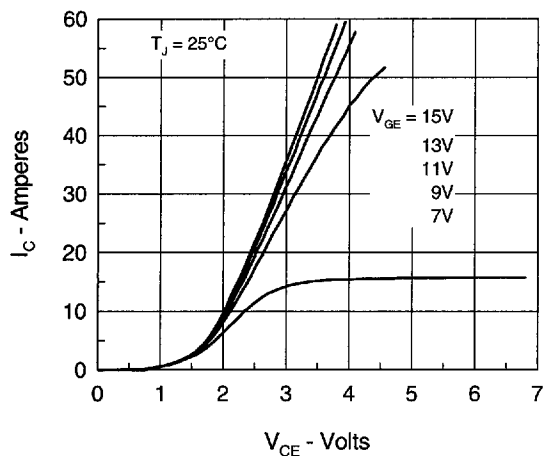
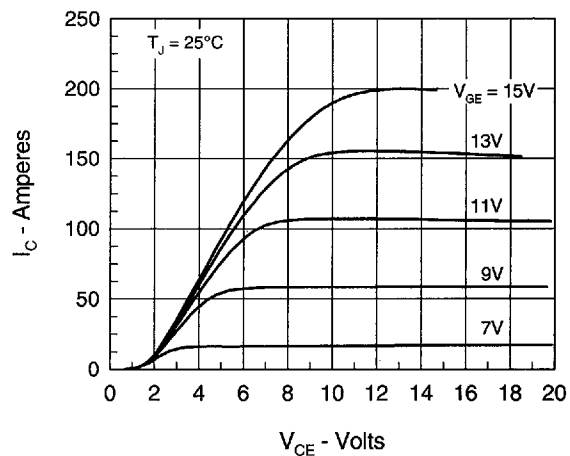
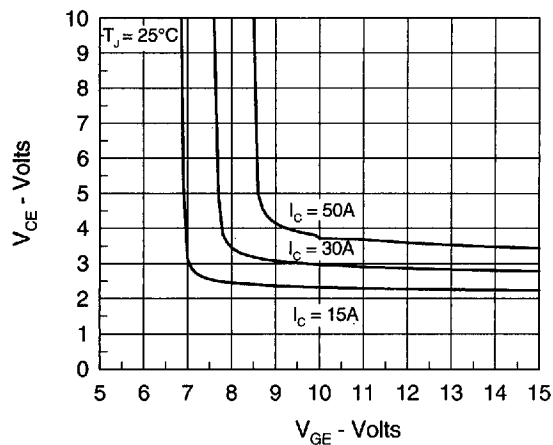
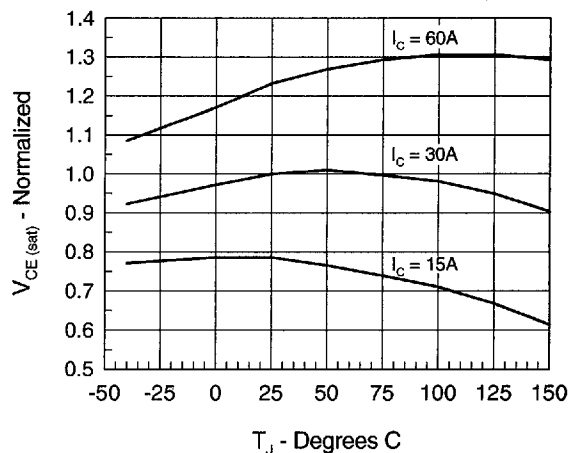
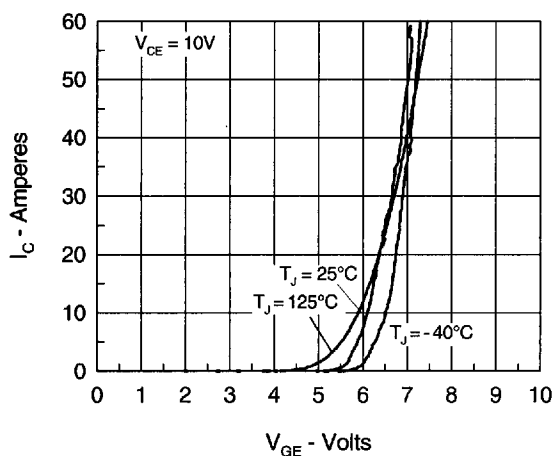
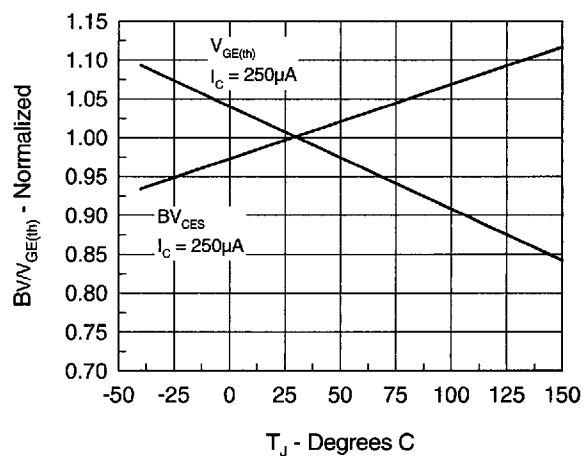
Fig. 1 Saturation Characteristics

Fig. 2 Output Characteristics

Fig. 3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

Fig. 4 Temperature Dependence of Output Saturation Voltage

Fig. 5 Input Admittance

Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current

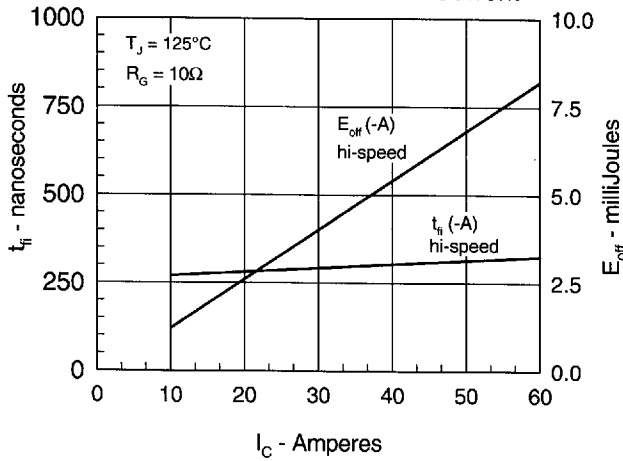


Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on R_G

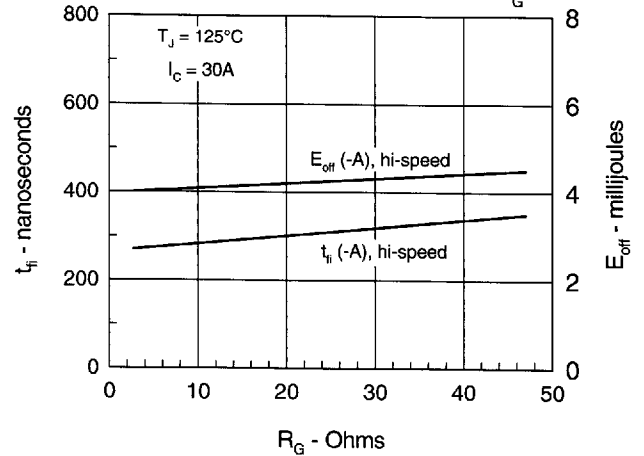


Fig.9 Gate Charge Characteristic Curve

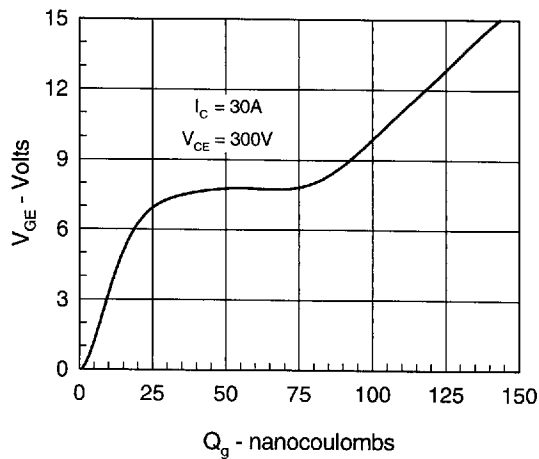


Fig.10 Turn-Off Safe Operating Area

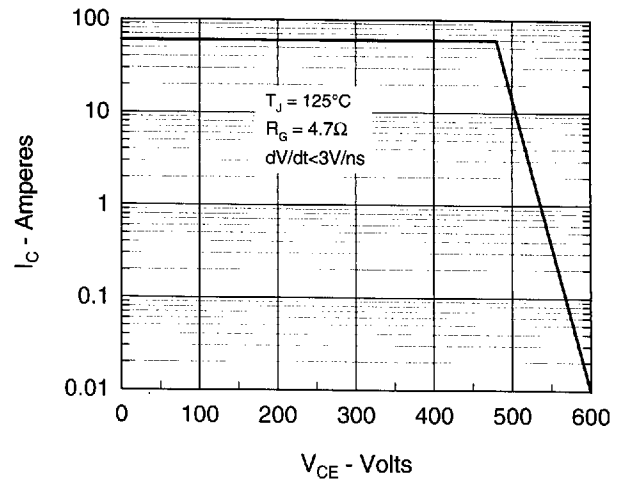


Fig.11 Transient Thermal Impedance

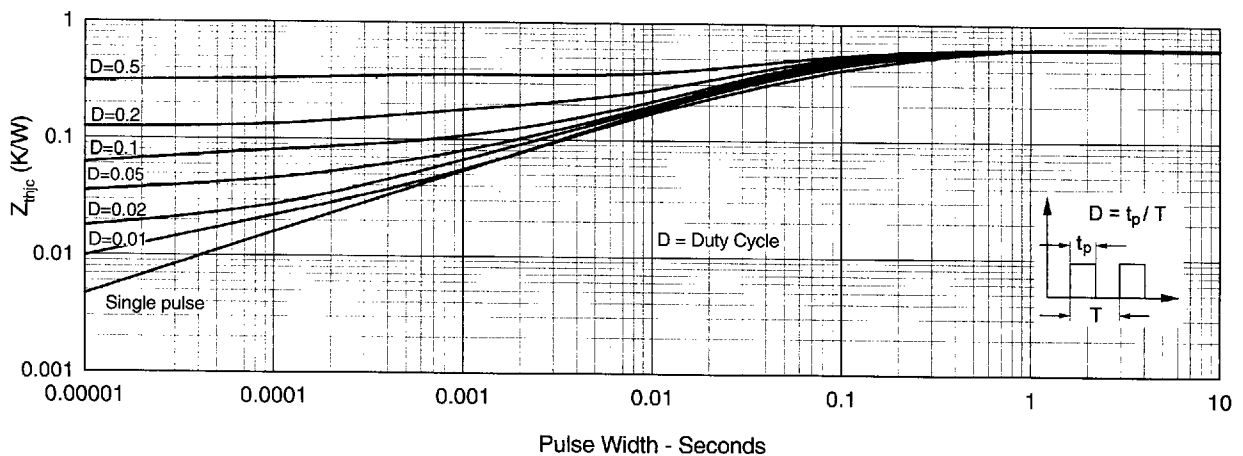


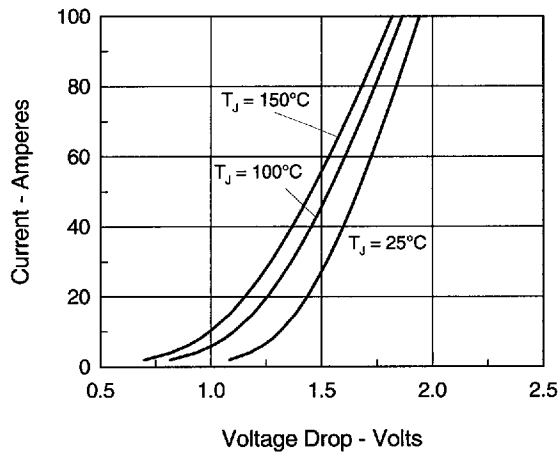
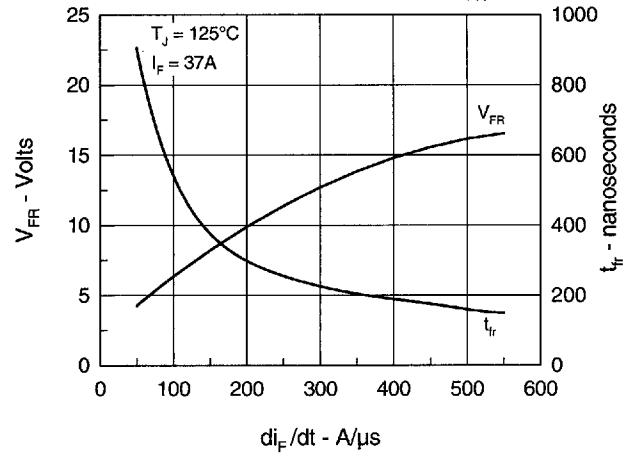
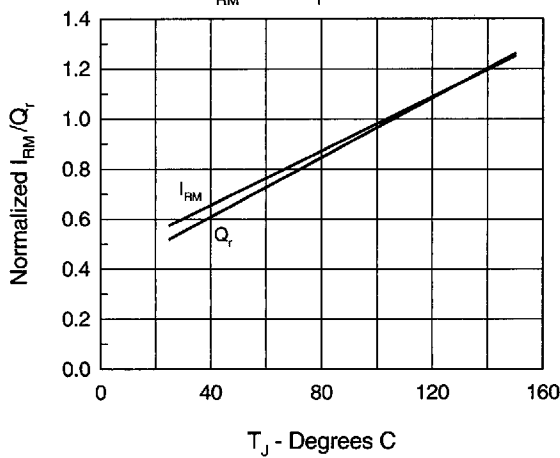
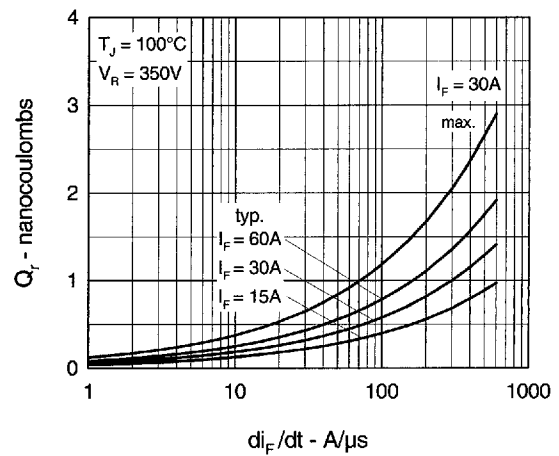
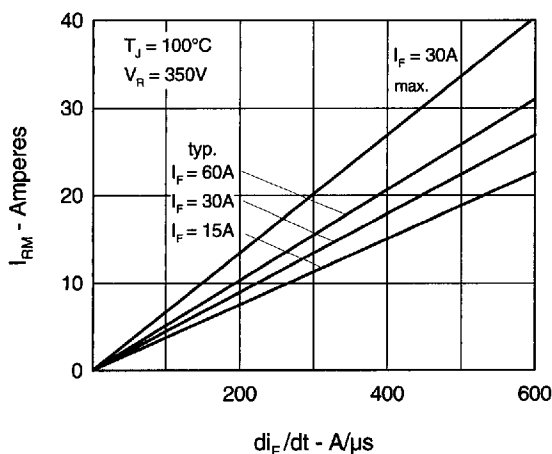
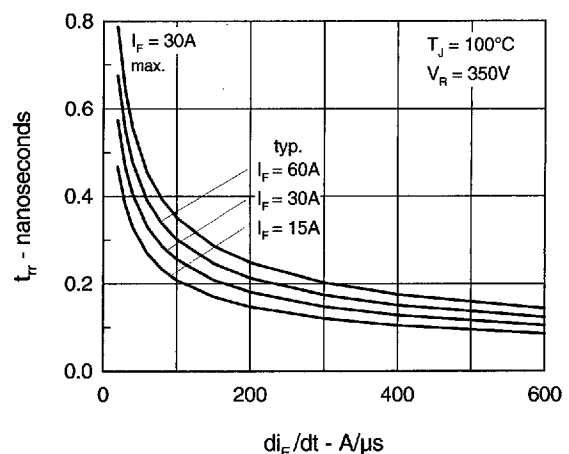
Fig.12 Maximum Forward Voltage Drop

Fig.13 Peak Forward Voltage V_{FR} and Forward Recovery Time t_{fr}

Fig.14 Junction Temperature Dependence of I_{RM} and Q_r

Fig.15 Reverse Recovery Charge Q_r

Fig.16 Peak Reverse Recovery Current I_{RM}

Fig.17 Reverse Recovery Time t_{rr}


Fig.17 Diode Transient Thermal resistance junction to case

